2SA1128

Silicon PNP epitaxial planer type

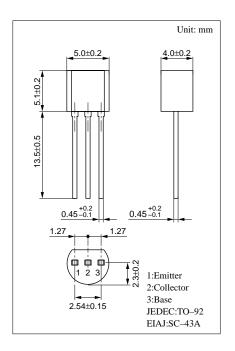
For low-frequency output amplification

Features

- ullet Low collector to emitter saturation voltage $V_{\text{CE(sat)}}$.
- Optimum for low-voltage operation and for converter circuits.

Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Ratings | Unit |
|------------------------------|------------------|-------------------|------|
| Collector to base voltage | V_{CBO} | -25 | V |
| Collector to emitter voltage | V _{CEO} | -20 | V |
| Emitter to base voltage | V _{EBO} | -7 | V |
| Peak collector current | I_{CP} | -1 | A |
| Collector current | I_{C} | - 0.5 | A |
| Collector power dissipation | P_{C} | 600 | mW |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T_{stg} | −55 ~ +150 | °C |



Electrical Characteristics (Ta=25°C)

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|----------------------|--|-----|-----|-------|------|
| Collector cutoff current | I_{CBO} | $V_{CB} = -25V, I_{E} = 0$ | | | -100 | nA |
| | I_{CEO} | $V_{CE} = -20V, I_B = 0$ | | | -1 | μА |
| Collector to base voltage | V _{CBO} | $I_{\rm C} = -10\mu{\rm A},\ I_{\rm E} = 0$ | -25 | | | V |
| Collector to emitter voltage | V _{CEO} | $I_{C} = -1 \text{mA}, I_{B} = 0$ | -20 | | | V |
| Emitter to base voltage | V _{EBO} | $I_{\rm E} = -10\mu A, I_{\rm C} = 0$ | -7 | | | V |
| Forward current transfer ratio | h _{FE1} *1 | $V_{CE} = -2V, I_C = -0.5A^{*2}$ | 90 | | 220 | |
| | h _{FE2} | $V_{CE} = -2V, I_{C} = -1A^{*2}$ | 25 | | | |
| Collector to emitter saturation voltage | V _{CE(sat)} | $I_C = -500 \text{mA}, I_B = -50 \text{mA}^{*2}$ | | | - 0.4 | V |
| Base to emitter saturation voltage | V _{BE(sat)} | $I_C = -500 \text{mA}, I_B = -50 \text{mA}^{*2}$ | | | -1.2 | V |
| Transition frequency | f_T | $V_{CB} = -10V$, $I_E = 50$ mA, $f = 200$ MHz | | 150 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = -10V, I_E = 0, f = 1MHz$ | | 15 | 25 | pF |

^{*2} Pulse measurement

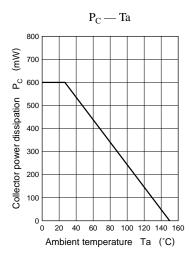
^{*1}hFE Rank classification

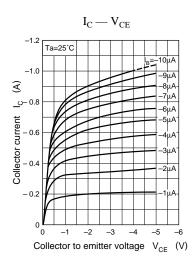
| Rank | Q | R |
|---------------|----------|-----------|
| $h_{\rm FE1}$ | 90 ~ 155 | 130 ~ 220 |

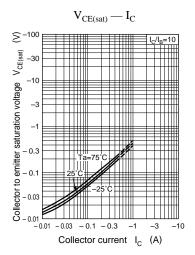
Note) S Rank $V_{CEO} \ge 18V$.

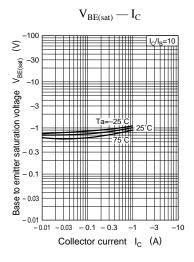
Panasonic

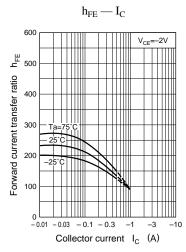
Transistor 2SA1128

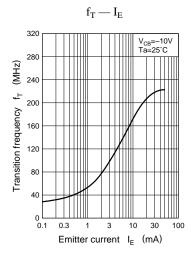


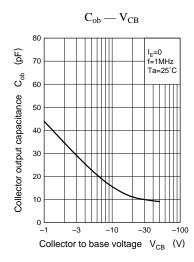












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